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## Test results of the first 4H-SiC LGAD from NJU China

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SiC as a typical wide bandgap semiconductor material has the potential to be used in the high energy field thanks to its good performance under radiation environment as well as running without cooling compared with traditional Si devices. Followed by the previous study of the timing performance of the 4H-SiC PIN device, a first 4H-SiC LGAD has been fabricated by Nanjing University (NJU) China. The device has 20 $\mu$ m active layer and 0.15 $\mu$ m gain layer. The preliminary test results of the electrical properties and response from alpha particle will be presented.

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